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PRESS RELEASE

MicroWave Technology Inc.

An IXYS Company

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January 12, 2009 -- Fremont, Calif. – MicroWave Technology Inc. (MwT), An IXYS Corporation (Nasdaq: IXYS), announced that it has introduced a family of three high linearity and high efficiency RF power amplifier products with output power up to 10 watts based on advanced high reliability GaN device technology. These new power amplifiers are the MGA-242740-02, MGA-333840-02, and MGA-495940-02, targeted at 802.16d/e WiMax applications and also 802.11a/b/g/n WLAN related applications with three frequencies bands, 2.4 – 2.7 GHz, 3.3 - 3.8 GHz, 4.9 – 5.9 GHz GHz, respectively. All three parts have high output power of 10 Watt (40 dBm) measured at 3 dB gain compression point and linear power gain range from 12 – 15 dB. These GaN based RF power amplifier parts have achieved extraordinary 23% power added efficiency at 2W (33dBm) linear power (burst power) with 2.5% EVM (Error-Vector-Magnitude) under the 64 QAM 802.16 WiMax digital signal modulation scheme.

“The linear power efficiency achieved by those GaN based power amplifiers is exceptional and is more than twice the performance of the GaAs or Silicon LDMOS based PA counter parts. We have



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demonstrated the superiority of GaN based power devices for the high power applications we target and also the advanced power microwave/RF amplifier design capabilities of our company," commented by Dr. Greg Zhou, general manager of MwT," We will continue to leverage the advantages of the microwave/RF GaN power device technology with high reliability and expand the product family to other applications that demand high linear power and power added efficiency performances including military and High Rel applications," .

The GaN based power amplifiers, biased at 28V on drain with quiescent current between 80 – 300 mA, are available in various packages including the low cost surface mount 02 packages. The MTBF (Mean-Time-Before-Failure) for those GaN based microwave/RF power amplifiers is over 100 years at 85C ambient temperature. Evaluation boards for the power amplifiers in 02 packages are available now. For detailed datasheets of GaN based power amplifiers and other MwT products please go to MwT's web site www.mwtinc.com. Contact RFMW, Ltd at sales@rfmw.com or call (877) FOR-RFMW (367-7369) for sample requests and price quote.